

B2 8. (Amended) A semiconductor light emitting device comprising:

a nitride-based semiconductor layer including an emission layer; and

a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein

said dielectric film contains a compound containing nitrogen and oxygen formed directly on

the surface of said nitride-based semiconductor layer while containing an oxide formed on said compound.

B3 11. (Amended) A semiconductor light emitting device comprising:

a nitride-based semiconductor layer including an emission layer; and

a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein

said dielectric film contains a nitride formed directly on the surface of said nitride-based

semiconductor layer while containing a compound containing nitrogen and oxygen formed on said nitride.

B4 17. (Twice amended) A semiconductor light emitting device comprising:

an emission layer composed of a nitride-based semiconductor;

a cladding layer, formed on said emission layer, composed of a nitride-based semiconductor having a flat portion and a projection portion located on said flat portion; and

a layer of nitride-based semiconductor formed on said projection portion, wherein

said projection portion of said cladding layer and said layer formed on said projection portion form a ridge portion, and

said ridge portion has a side surface having a step formed between a side surface of  
said projection portion of said cladding layer and a side surface of said layer formed on said  
projection portion;

said semiconductor light emitting device further comprising a dielectric film formed on said flat  
portion of said cladding layer and the side surface of said ridge portion.

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